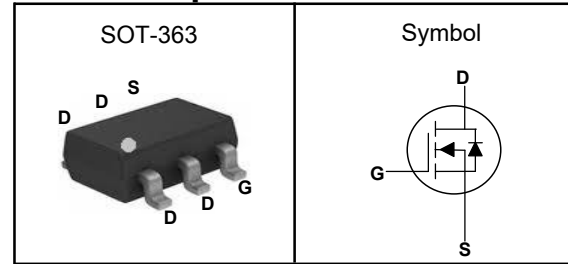


N-Channel Enhancement Mode MOSFET

Features

- Low R_{dson} for low conduction loss
- Reliable and Rugged
- ROHS Compliant & Halogen-Free

Pin Description



Applications

- Power Management in Desktop Computer
- DC/DC Converters

V _{DSS}	110	V
R _{DS(ON)-Typ}	200	mΩ
I _D	3	A

Absolute Maximum Ratings (T_A=25°C, Unless Otherwise Noted)

Symbol	Parameter	N-Channel	Unit
V _{DSS}	Drain-Source Voltage	110	V
V _{GSS}	Gate-Source Voltage	±20	V
T _J	Maximum Junction Temperature	-55 to 150	°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
I _{DM} ^①	Pulse Drain Current Tested	10	A
I _D	Continuous Drain Current	3	A
P _D	Maximum Power Dissipation	1.25	W

Thermal Characteristics

Symbol	Parameter	Rating	Unit
R _{θJA}	Thermal Resistance-Junction to Ambient	100	°C/W

Note ① : Max. current is limited by bonding wire.

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150°C.

Note ③ : Surface Mounted on 1in² FR-4 board with 1oz.

**N-Channel Enhancement Mode MOSFET****Electrical Characteristics** ($T_J=25^\circ\text{C}$, Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	110	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=110V, V_{GS}=0V$	---	---	1	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	---	2.5	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
$R_{DS(ON)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_D=1A$	---	200	230	m Ω
Dynamic Characteristics ^⑤						
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=50V,$ Freq.=1MHz	---	190	---	pF
C_{oss}	Output Capacitance		---	22	---	
C_{rss}	Reverse Transfer Capacitance		---	13	---	
$T_{d(on)}$	Turn-on Delay Time	$V_{DD}=50V, V_{GS}=10V,$ $R_G=1\Omega, I_D=1.3A,$ $R_L=39\Omega$	---	6	---	nS
T_r	Turn-on Rise Time		---	10	---	
$T_{d(off)}$	Turn-off Delay Time		---	10	---	
T_f	Turn-off Fall Time		---	6	---	
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=1A$	1	---	---	S
Q_g	Total Gate Charge	$V_{DS}=50V,$ $V_{GS}=10V, I_D=1.3A$	---	5.2	---	nC
Q_{gs}	Gate-Source Charge		---	0.75	---	
Q_{gd}	Gate-Drain Charge		---	1.4	---	
Source-Drain Characteristics ($T_J=25^\circ\text{C}$)						
V_{SD} ^④	Diode Forward Voltage	$I_S=1A, V_{GS}=0V$	---	---	1.2	V

Note ④ : Pulse test (pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$).

Note ⑤ : Guaranteed by design, not subject to production testing.

N-Channel Enhancement Mode MOSFET

Typical Characteristics

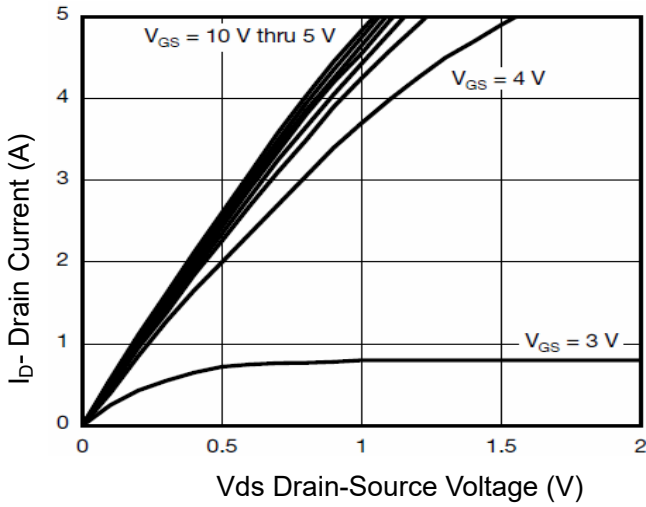


Figure 1 Output Characteristics

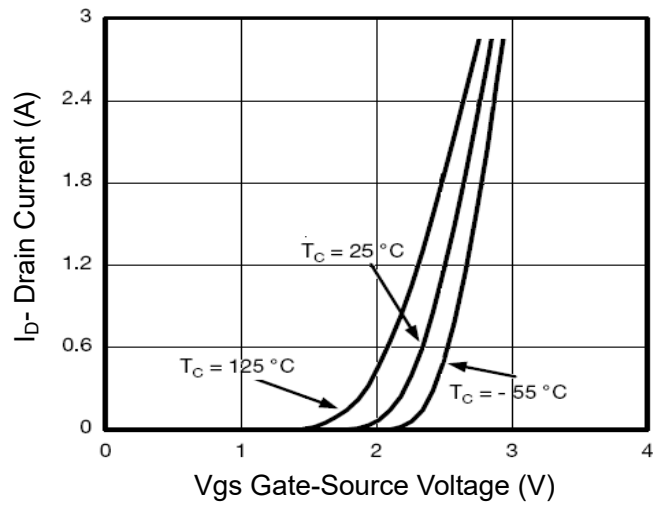


Figure 2 Transfer Characteristics

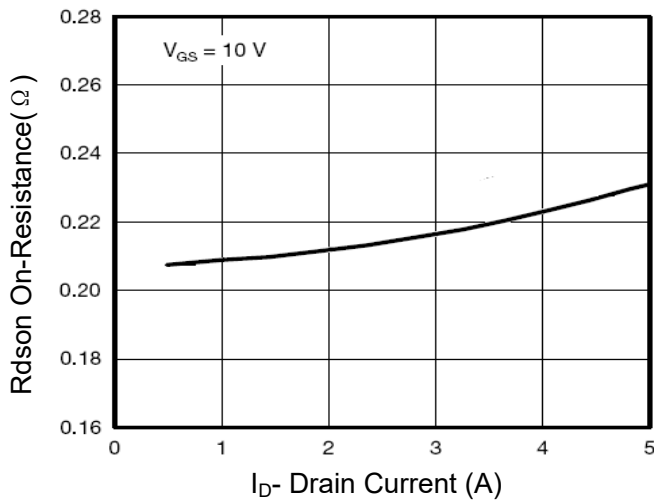


Figure 3 Rdson- Drain Current

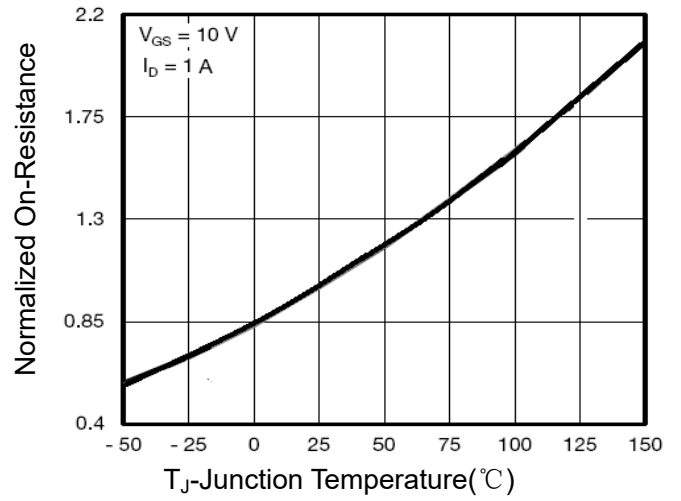


Figure 4 Rdson-Junction Temperature

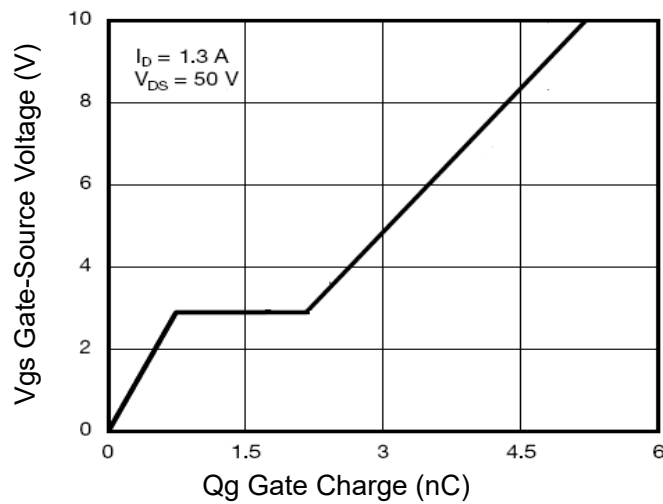


Figure 5 Gate Charge

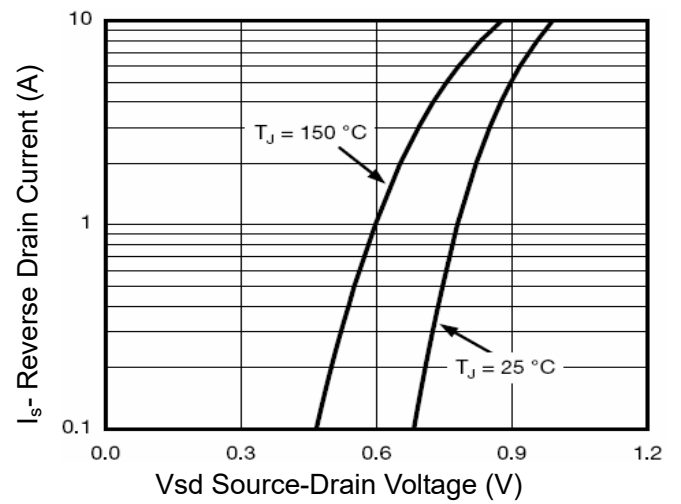


Figure 6 Source- Drain Diode Forward

N-Channel Enhancement Mode MOSFET

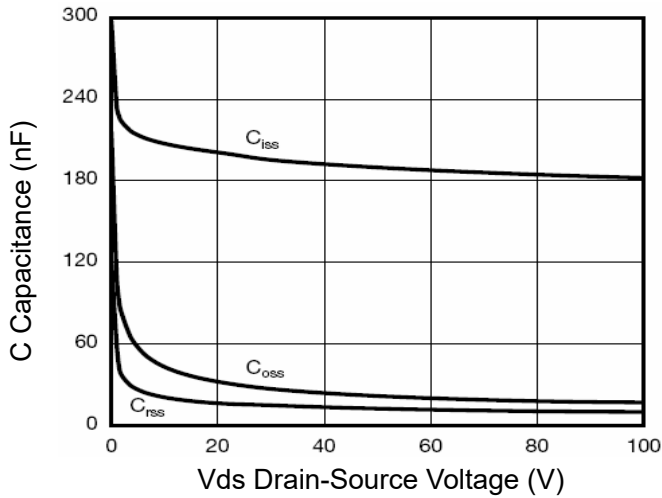


Figure 7 Capacitance vs Vds

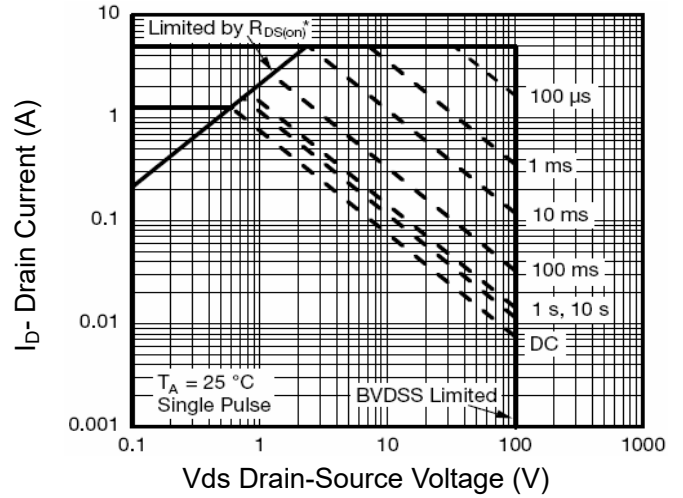


Figure 8 Safe Operation Area

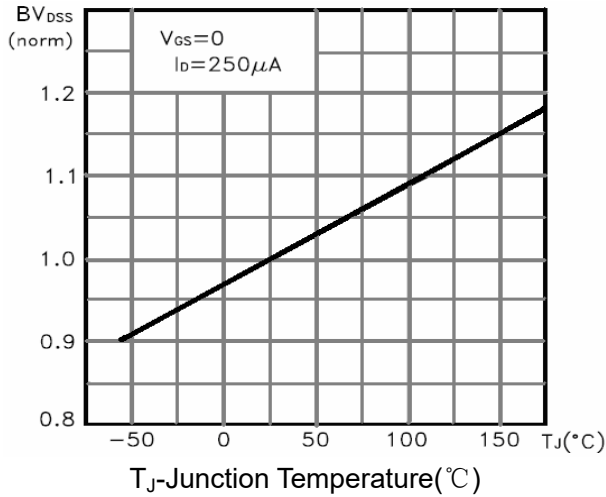


Figure 9 BV_{DSS} vs Junction Temperature

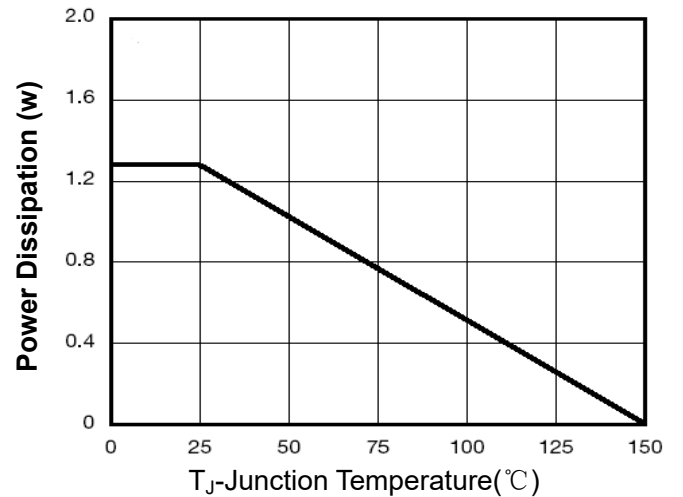


Figure 10 Power De-ratin

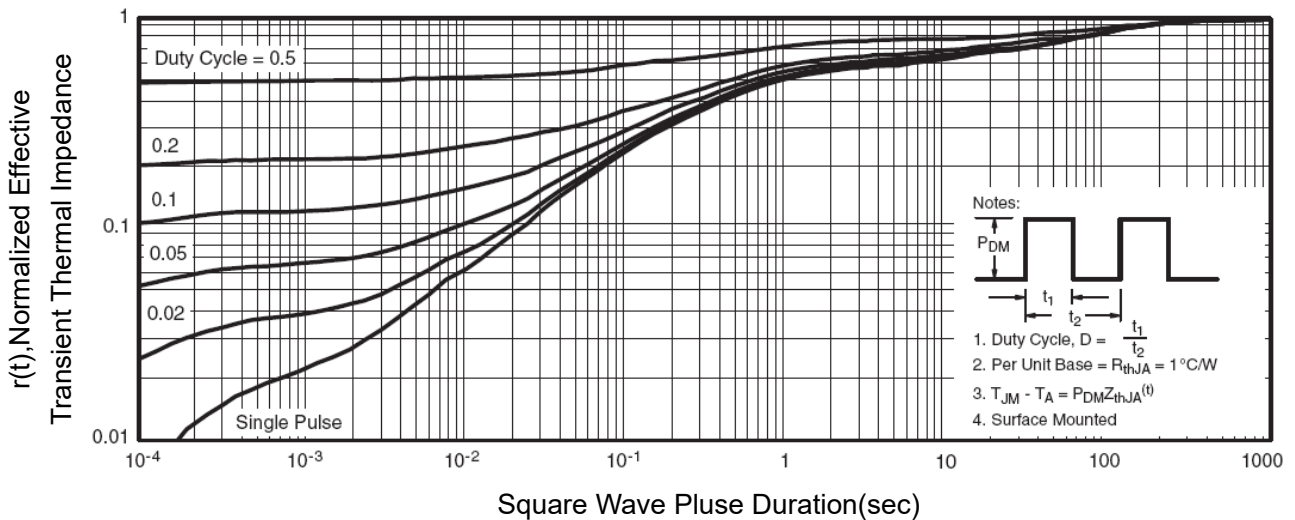
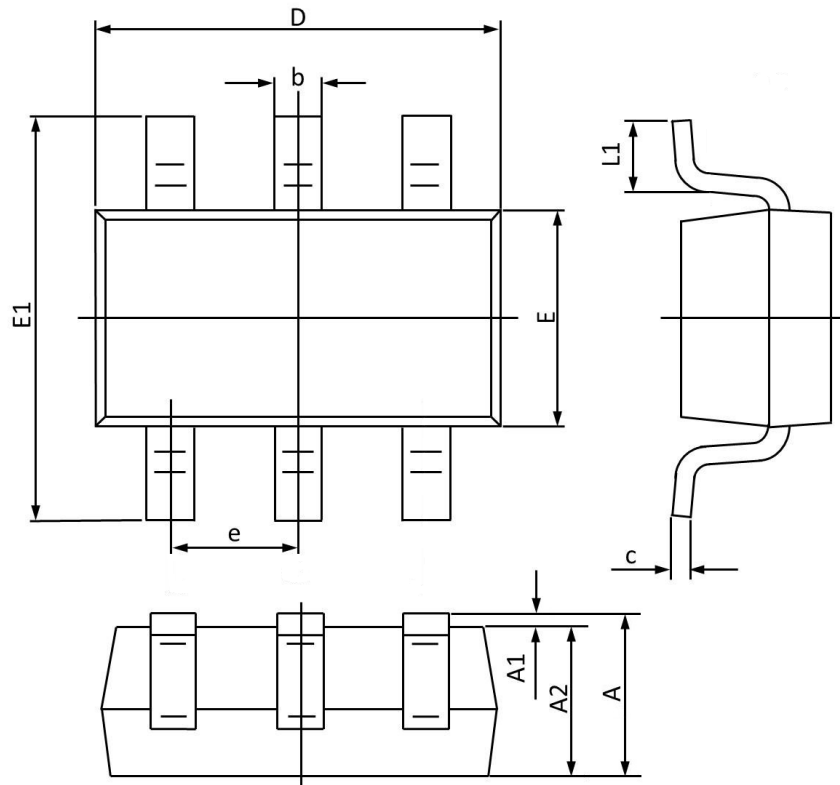


Figure 11 Normalized Maximum Transient Thermal Impedance

N-Channel Enhancement Mode MOSFET
SOT-363 Package Outline Dimensions


Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	0.80	0.95	1.10	D	1.80	2.00	2.20
A₁	--	--	0.10	E	1.15	1.25	1.35
A₂	0.80	0.90	1.00	E1	1.80	2.10	2.40
b	0.10	0.20	0.33	e	--	0.65	--
c	0.10	0.17	0.25	L1	0.10	0.20	0.35